

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC3668

Power Amplifier Applications  
Power Switching Applications

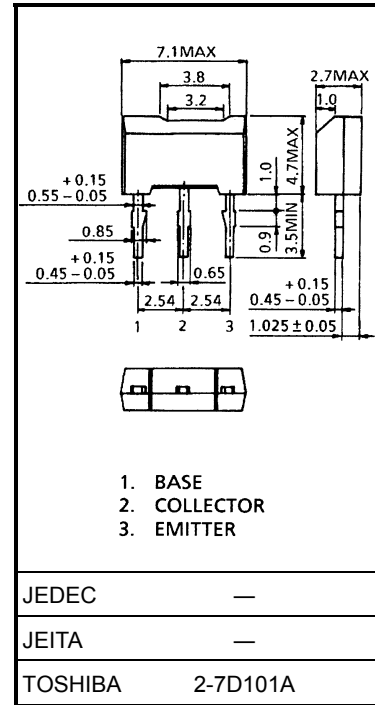
- Low saturation voltage:  $V_{CE(sat)} = 0.5\text{ V (max)}$  ( $I_C = 1\text{ A}$ )
- High collector power dissipation:  $P_C = 1000\text{ mW}$
- High-speed switching:  $t_{stg} = 1.0\text{ }\mu\text{ (typ.)}$
- Complementary to 2SA1428.

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	2	A
Base current	$I_B$	0.5	A
Collector power dissipation	$P_C$	1000	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to 150	$^\circ\text{C}$

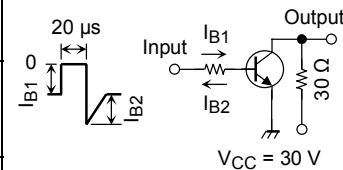
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



Weight: 0.2 g (typ.)

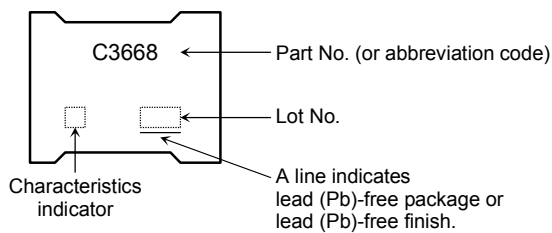
## Electrical Characteristics (Ta = 25°C)

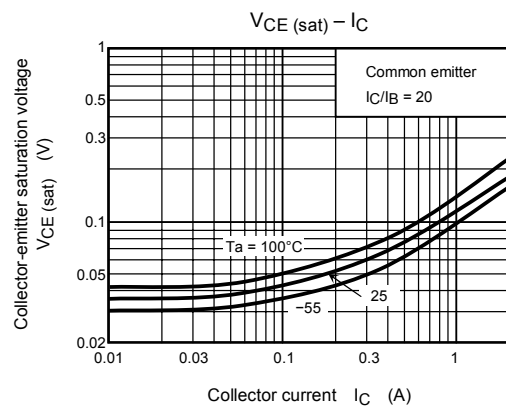
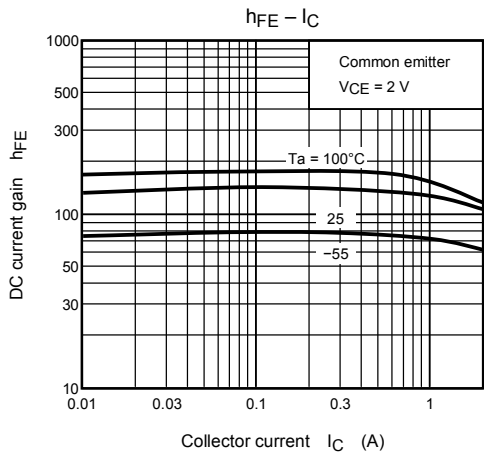
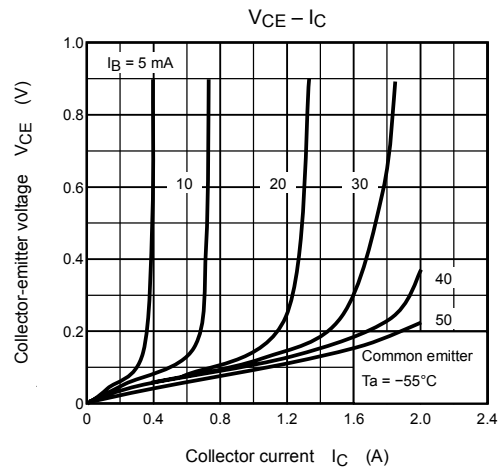
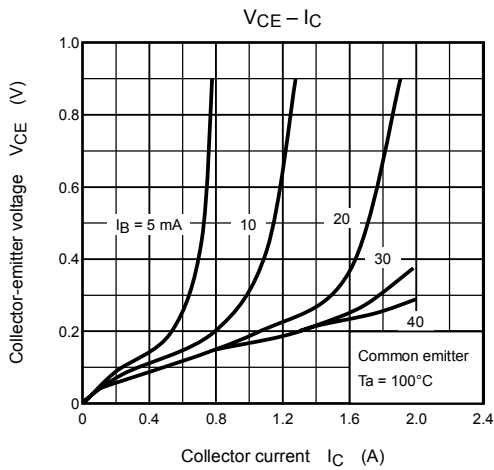
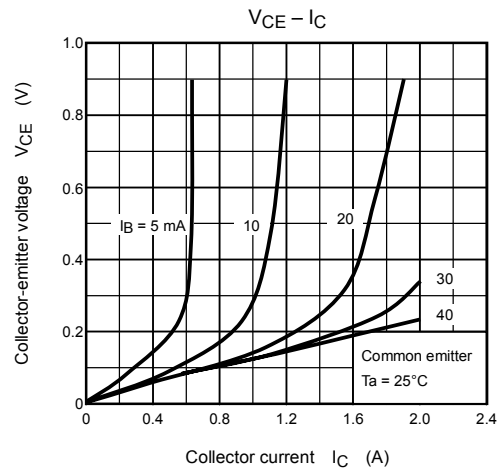
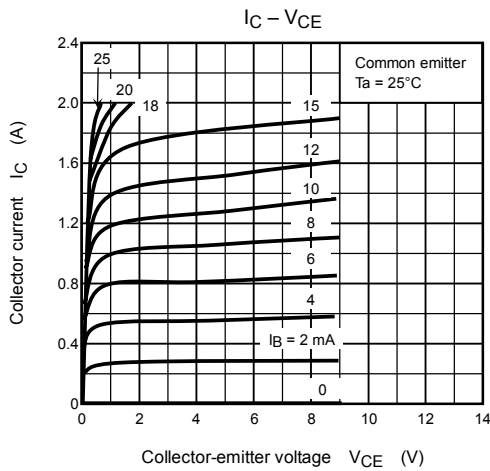
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		$I_{CBO}$	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	1.0	$\mu\text{A}$
Emitter cut-off current		$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	1.0	$\mu\text{A}$
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	50	—	—	V
DC current gain		$h_{FE(1)}$ (Note)	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	70	—	240	
		$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$	40	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 0.05\text{ A}$	—	—	0.5	V
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = 1\text{ A}, I_B = 0.05\text{ A}$	—	—	1.2	V
Transition frequency		$f_T$	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	100	—	MHz
Collector output capacitance		$C_{ob}$	$V_{CB} = 10\text{ V}, I_C = 0, f = 1\text{ MHz}$	—	30	—	pF
Switching time	Turn-on time	$t_{on}$		—	0.1	—	$\mu\text{s}$
	Storage time	$t_{stg}$		—	1.0	—	
	Fall time	$t_f$		—	0.1	—	

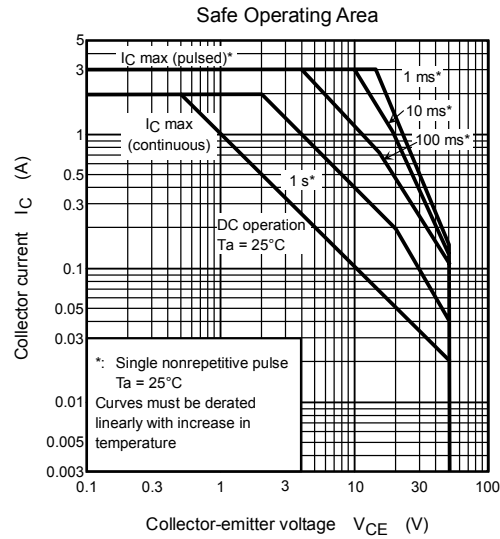
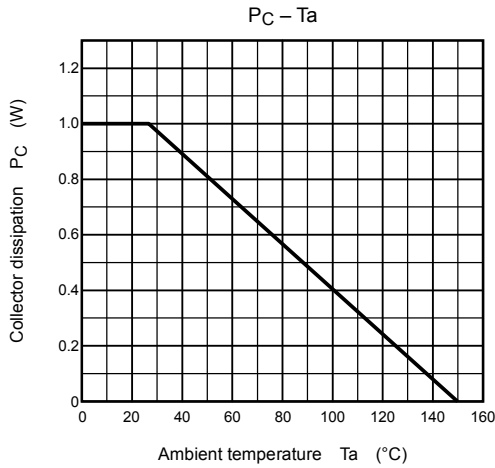
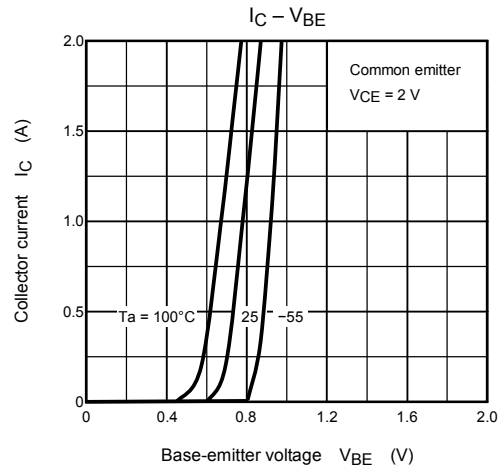
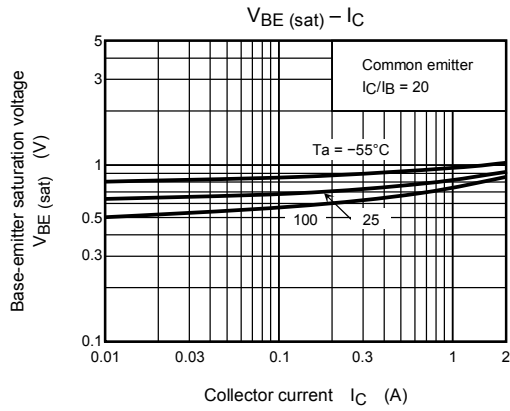
$I_{B1} = -I_{B2} = 0.05\text{ A}, \text{ duty cycle} \leq 1\%$

Note:  $h_{FE(1)}$  classification O: 70 to 140, Y: 120 to 240

## Marking







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